

Dimer with Thermally Activated Delayed Fluorescence (TADF) Emission in Non-Doped Device

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1. Experimental Section

1.1 Materials and instruments

The raw reagents, catalysts and chemicals involved in the initial reaction were purchased from commercial sources and used without further purification. Tetrahydrofuran (THF), and 1,4-dioxane used in synthetic routes were purified by PURE SOLV (Innovative Technology) purification system. The ^1H NMR and ^{13}C NMR spectra were measured on Bruker 400 and Bruker 600 spectrometer in deuterated chloroform solvent with trimethylsilane (TMS) as reference. Matrix-Assisted Laser Desorption/ Ionization Time of Flight Mass Spectrometry MS-MALDI (TOF) was performed using a Bruker Autoflex II / Compass 1.0. The ultraviolet–visible (UV–vis) absorption spectra were measured by a Shimadzu UV-2600 spectrophotometer. Fluorescent and phosphorescent spectra were measured by a Hitachi F-4600 and FLUOROMAX-4 spectrophotometer. Thermogravimetric analysis (TGA) was measured by a METTLER TOLEDO TGA1 under high purity nitrogen atmosphere. The temperature was increased to 800 °C with a heating rate of 10 °C/minute. Electrochemical analysis was achieved on a CHI 600D electrochemical work station, and the scan rate was 100 mV S⁻¹ at room temperature. The three-electrode configuration system in *n*-Bu₄NPF₆ (0.1 M) CH₂Cl₂ solution. The redox potential of ferrocene/ferrocenium (Fc/Fc⁺) was measured under room temperature (for calibration). The PLQY was measured using Hamamatsu C9920-02G in nitrogen or air atmosphere. Transient spectra were obtained by using the Quantaaurus-Tau fluorescence lifetime measurement system (C11367-03, Hamamatsu Photonics Co.) in vacuum or nitrogen atmosphere. Elemental analysis was measured using Vario Micro cube.

1.2 Device fabrication process

OLED devices were fabricated on ITO glass substrates (130 nm, 15 Ω/sq) under a base pressure of 4×10⁻⁶ Torr and the active area of the devices was 0.1 cm². The substrate was ultrasonically cleaned sequentially with acetone, ethanol, and deionized water, and dried in an oven at 120 °C for 5 h. Then, it was treated with ultraviolet ozone for 15 mins before placing it in a vacuum chamber. All organic materials' deposited rates were

2 Å/s, and Al's is 6-8 Å/s. The deposition rate of the dopant was adjusted according to the volume ratio doped in the host materials. Quartz crystals would monitor all materials' deposition rate and thickness.

The EL information such as EL spectra, current efficiency (CE), power efficiency (PE), CIE coordinate, voltage of device and luminance were all recorded via a programmable spectrum scan photometer (PHOTO RESEARCH, PR 655) and KEITHLEY 2400 source meter. All the measurements were conducted in ambient air at room temperature, and the external quantum efficiency was calculated assuming Lambertian distribution of light emission.

1.3 DFT Methods.

All optimizations are finished at PBE0/def2-SVP level with Grimme's D3BJ ^[1] empirical dispersion correction. The relaxed excited states are optimized at TD-CAM-B3LYP/def2-SVP level with GD3BJ correction. The transition energies are PCM solvation model used with diphenyl ether as solvent. The dielectric constant of diphenyl ether is 3.73, which resemble the environment of organic solids. All the calculations are performed by the Gaussian 09 program and the hole-electron distribution analysis is performed by the Multiwfn program. ^[2]

2. Supporting Figures

2.1 Experimental data of synthesis

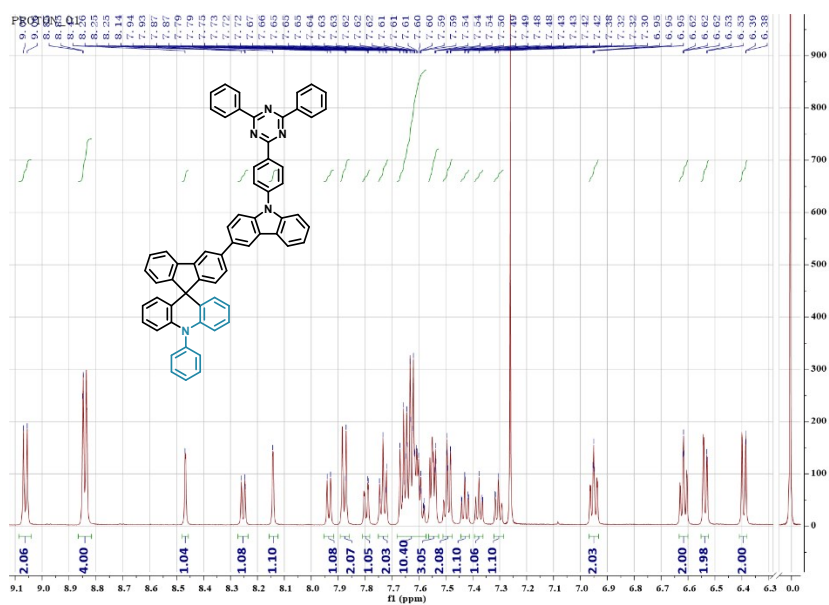


Figure S1. 600 MHz ^1H NMR spectrum of SFCCN measured in CDCl_3 .

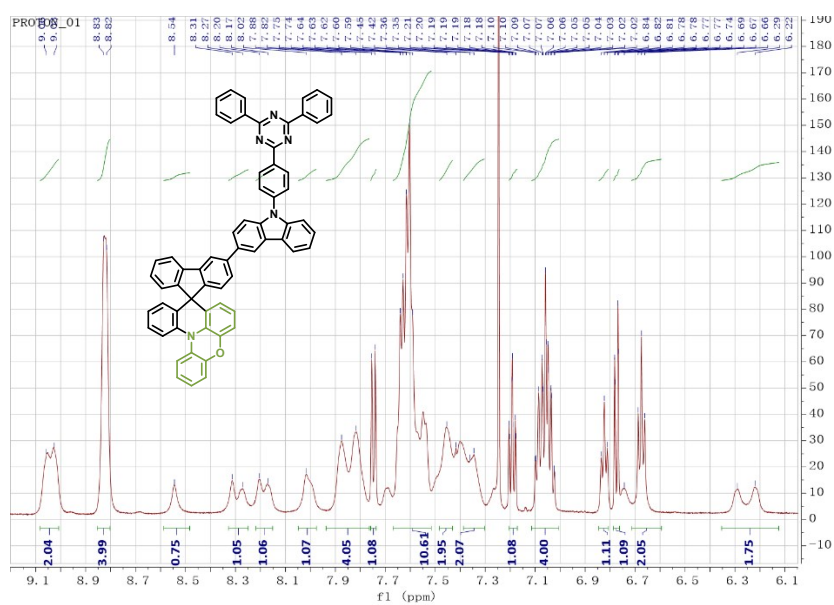


Figure S2. 600 MHz ^1H NMR spectrum of SFCCNO measured in CDCl_3 .

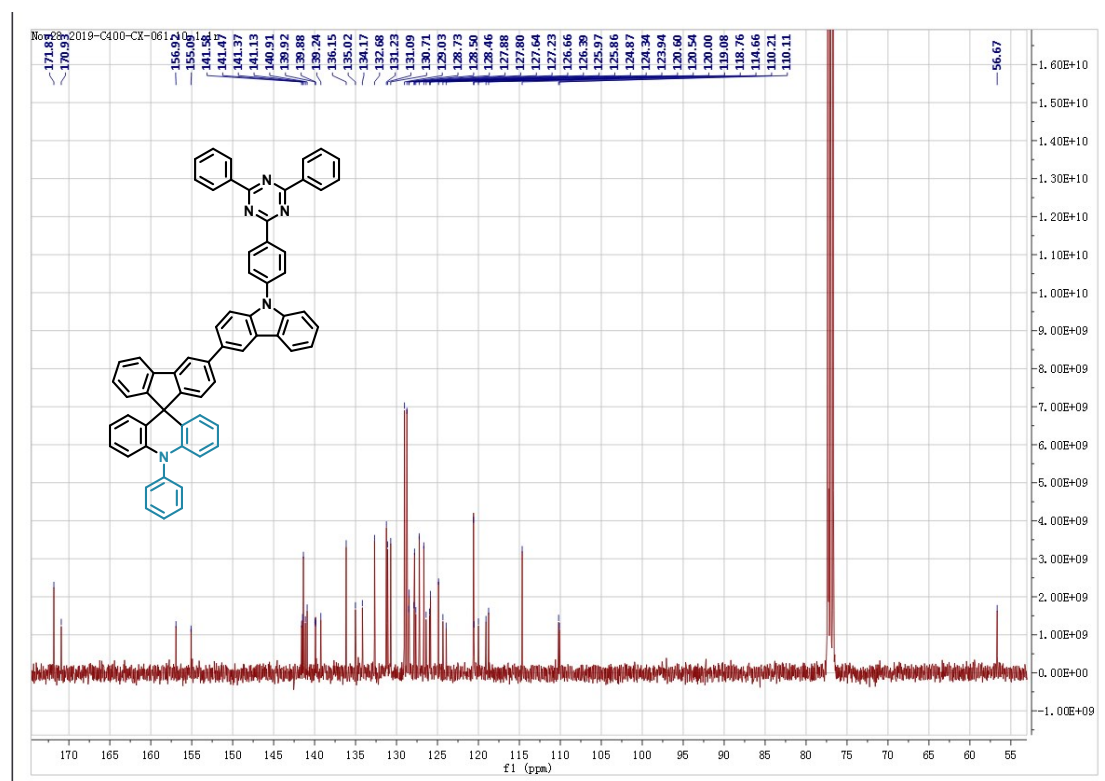


Figure S3. 101 MHz ^{13}C NMR spectrum of SFCCN measured in CDCl_3 .

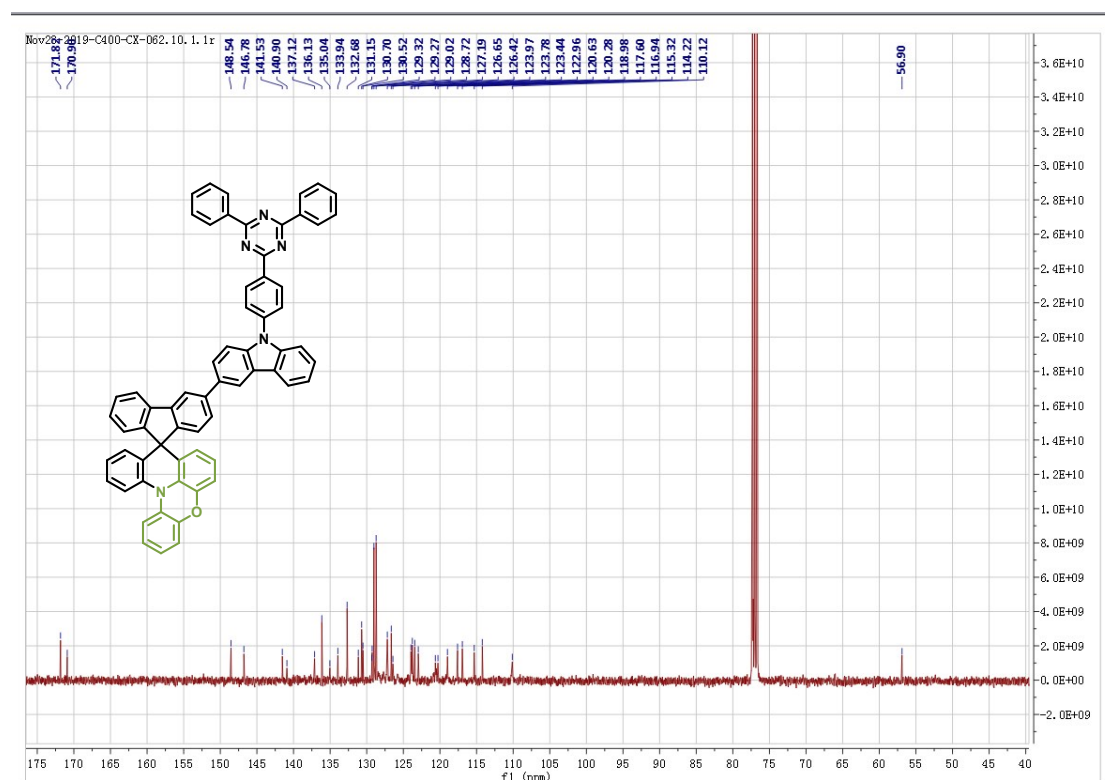


Figure S4. 101 MHz ^{13}C NMR spectrum of SFCCNO measured in CDCl_3 .

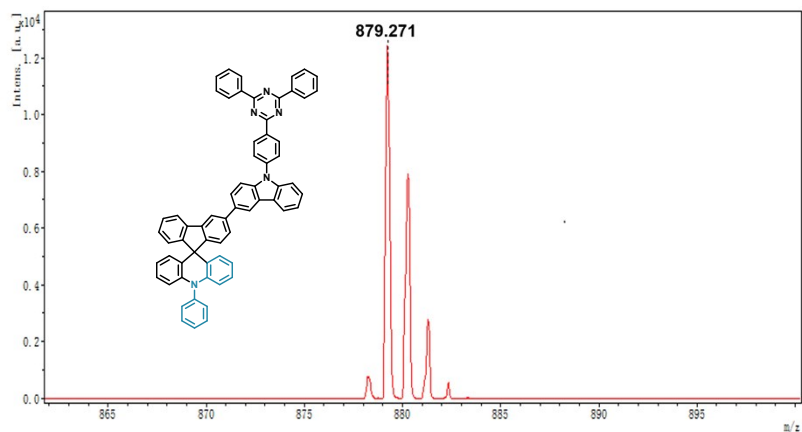


Figure S5. MALDI-TOF spectrum of SFCCN.

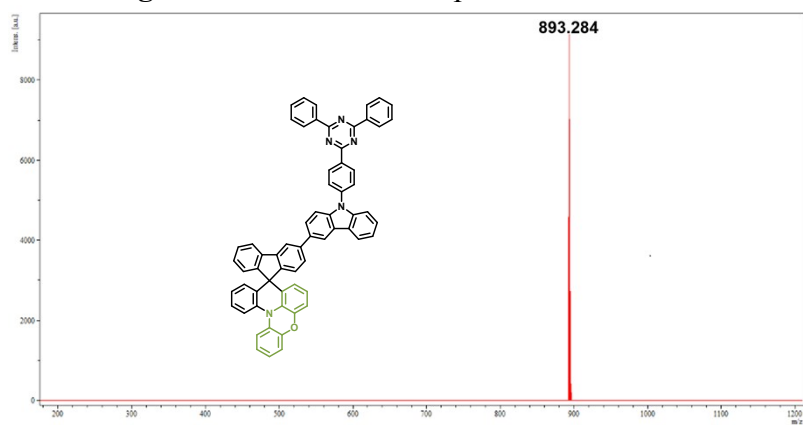


Figure S6. MALDI-TOF spectrum of SFCCNO.

2.2 Thermal properties

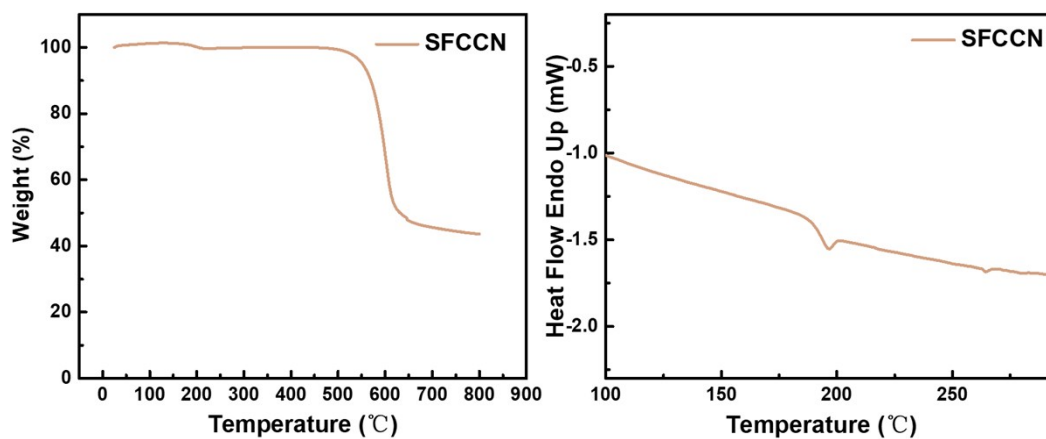


Figure S7. Thermal gravimetric analysis (TGA) curve and differential scanning calorimeter (DSC) curve of SFCCN.

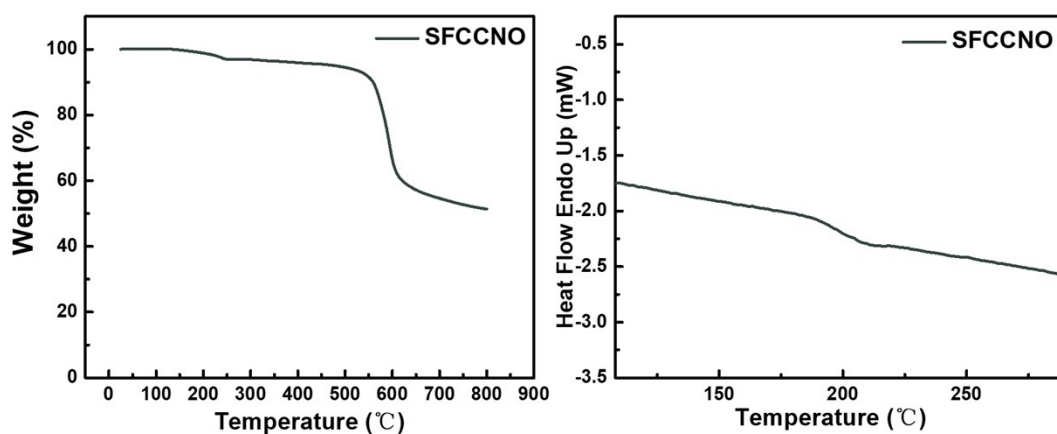


Figure S8. Thermal gravimetric analysis (TGA) curve and differential scanning calorimeter (DSC) curve of **SFCCNO**.

2.3 Photophysical properties

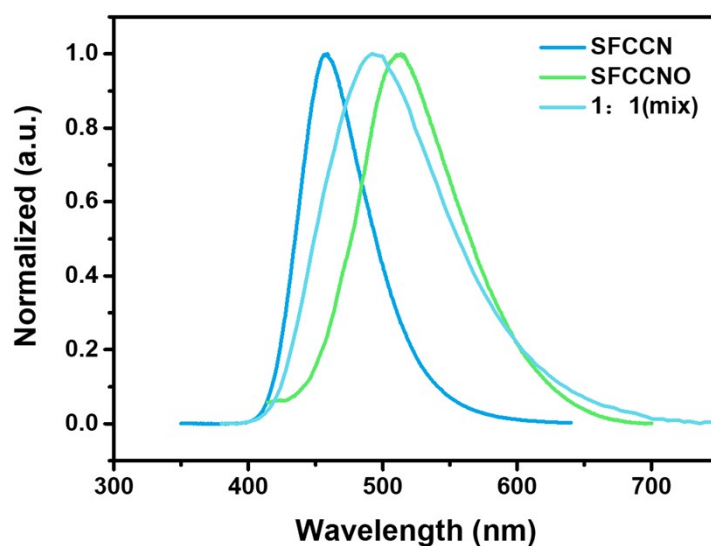


Figure S9. The neat film fluorescence spectra of **SFCCN**, **SFCCNO** and **SFCCN:SFCCNO (mix)**

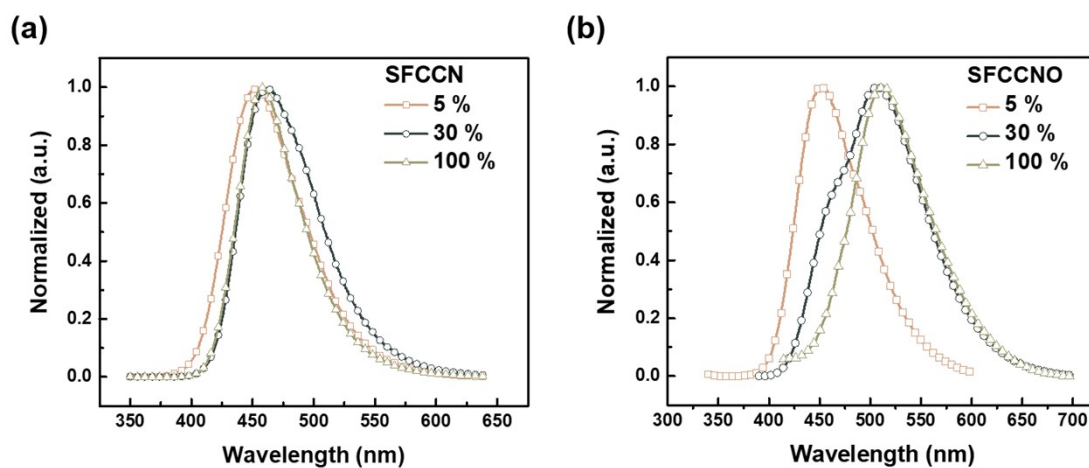


Figure S10. Fluorescence spectra of (a) DPEPO: **SFCCN** and (b) DPEPO: **SFCCNO** in film state.

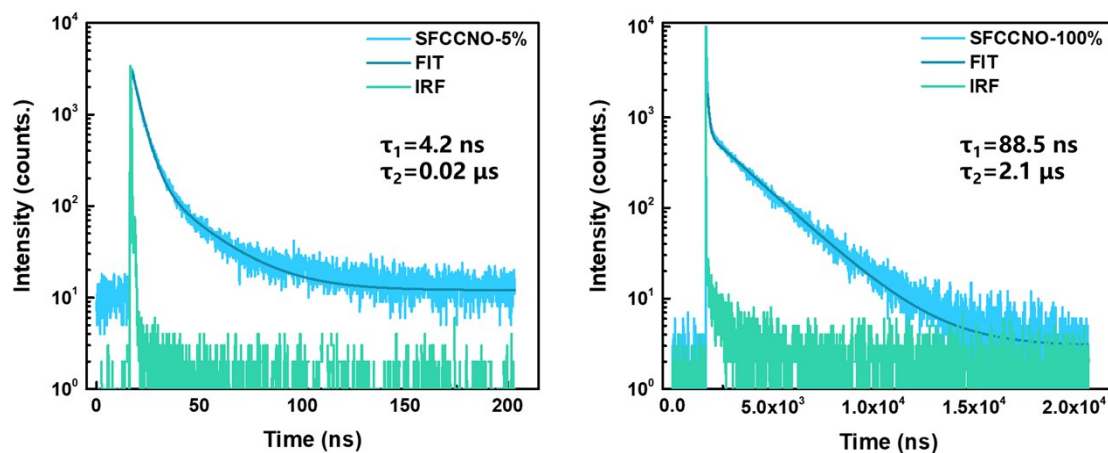


Figure S11. Transient photoluminescence spectra of DPEPO: **SFCCNO** (5 wt %) and pristine **SFCCNO** in film state.

2.4 Electrochemical properties

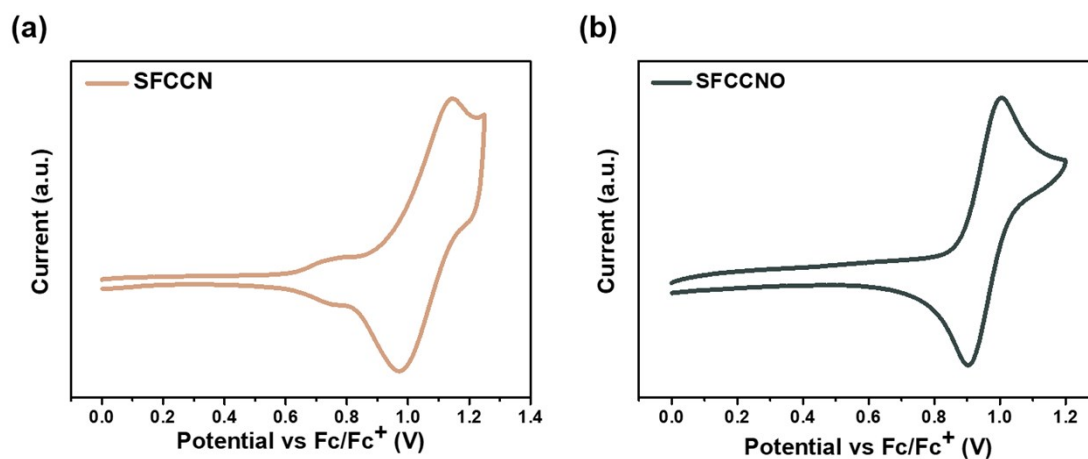


Figure S12. Cyclic voltammogram of the **SFCCN** and **SFCCNO**.

2.5 DFT data

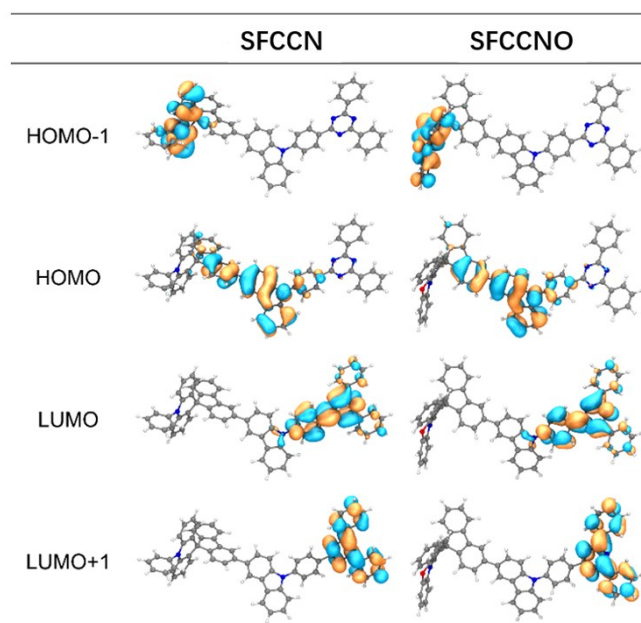


Figure S13. Frontier orbital distributions of SFCCN and SFCCNO.

2.6 EL spectra

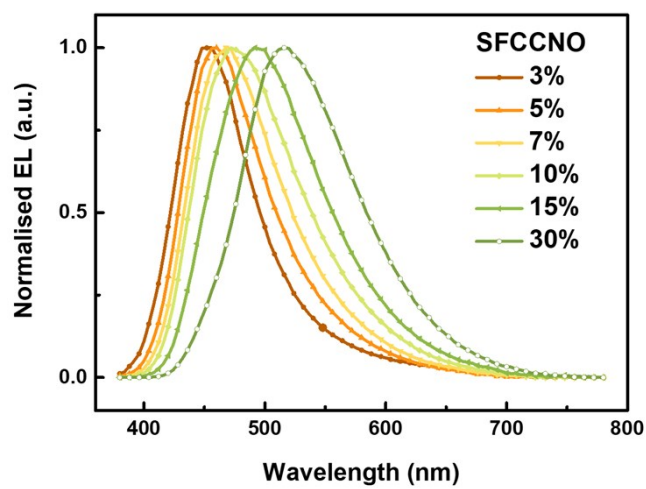


Figure S14. EL spectra of DPEPO: SFCCNO in film state.

3. Supporting Tables

3.1 DFT data

Table S1. Calculated properties of adiabatic S_1 and T_1 states and ΔE_{ST} .

	S_1			T_1		ΔE_{ST} (eV)
	λ (nm)	f	orbitals	λ (nm)	orbitals	
SFCCN	451.89	0.3729	H1-L:0.963	549.51	H1-L:0.576	0.44
SFCCNO	458.07	0.0991	H1-L:0.957	549.89	H1-L:0.591	0.40
SFCCNO dimer	654.91	0.003	H-L:0.997	666.05	H-L:0.989	0.05

Table S2 Calculated frontier orbital levels of **SFCCN** and **SFCCNO** in their ground state

	HOMO-1	HOMO	LUMO	LUMO+1
SFCCN	-5.716	-5.438	-2.098	-2.026
SFCCNO	-5.766	-5.288	-2.118	-2.043

Table S3. Calculated properties of first three singlet states and triplet states at relaxed S_1 and T_1 geometries, respectively.

	S_1				T_1		
	eV	nm	f	Orbitals	eV	nm	Orbitals
SFCCN	2.744	451.89	0.3729	H1-L:1.0	2.256	549.51	H1-L:0.576
	2.860	433.51	0.0000	H-L:0.94	2.752	450.59	H2-L3:0.149
	3.362	368.8	0.0001	H1-L1:0.95	2.945	420.99	H-L:0.996
SFCCNO	2.784	445.37	0.3991	H1-L:0.96	2.255	549.89	H1-L:0.591
	2.707	458.07	0.0070	H-L:0.95	2.756	449.85	H1-L2:0.16
	3.221	384.94	0.0000	H-L1:1.0	2.773	447.09	H-L:0.929
dimer	1.893	654.91	0.003	H-L:1.0	1.862	666.05	H-L:0.989
	2.457	504.54	0.0005	H-L3:1.0	2.439	508.32	H-L3:0.981
	2.713	457.08	0.0005	H-L1:1.0	2.517	492.62	H3-L:0.495

3.2 EL performance

Table S4. The EL proprieties with 3-30 wt % doping ratio of **SFCCN** and **SFCCNO**

	Doping ratio (%)	Peak ^a (nm)	FWMH ^a (nm)	Max CE/ PE/ EQE ^b (cd·A ⁻¹ / lm·W ⁻¹ / %)	CIE (x, y) ^a
SFCCNO	3	456	75	2.5/ 1.2/ 1.9	(0.17, 0.15)
	5	460	81	4.2/ 1.9/ 2.5	(0.17, 0.20)
	7	468	89	11.5/ 7.0/ 6.1	(0.18, 0.23)
	10	472	102	14.0/ 9.4/ 6.5	(0.20, 0.28)
	15	492	107	26.5/ 19.3/ 10.6	(0.22, 0.37)
	30	516	95	36.5/ 30.9/ 12.9	(0.29, 0.48)
SFCCN	5	460	70	4.5/ 2.5/ 3.3	(0.15,0.15)
	30	472	74	18.5/ 15.1/ 10.0	(0.16,0.23)

a. Measured at a driving current density at 5 mA cm⁻²; b. maximum data of current efficiency, power efficiency and external quantum efficiency.

4 References

1. G. Stefan, E. Stephan, G. Lars, *J. Comput. Chem.*, 2011, **32**, 1456–1465.
2. L. Tian, F. -W. Chen, *J. Comput. Chem.*, 2012, **33**, 580–92.